NXPSC04650X



Product data sheet

1. General description

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Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- High forward surge capability I_{FSM}
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions Values					Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		650				V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h ≤ 104 °C; Fig. 1; Fig. 2; Fig. 3	4			A	
Symbol	Parameter	Conditions	Min Typ Max				Unit
Static characteristics							
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 4 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K IA A
2	А	anode	oOo	K <u>– K</u> 001aaa020
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information										
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date				
NXPSC04650X	TO220F-2L	NXPSC04650X6Q	Tube	50	TO220FN-2L	20-July-2016				

7. Marking

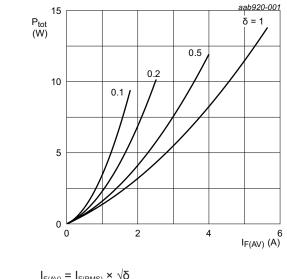
Table 4. Marking codes	
Type number	Marking codes
NXPSC04650X	NXPSC 04650X

8. Limiting values

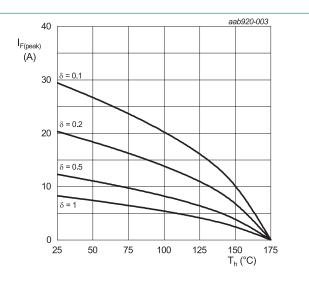
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V _{RWM}	crest working reverse voltage		650	V
V _R	reverse voltage	DC	650	V
$\boldsymbol{I}_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; T _h ≤ 104 °C; Fig. 1; Fig. 2; Fig. 3	4	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 µs; T _h ≤ 104 °C; square-wave pulse	8	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	24	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	235	А
l ² t	I ² t for fusing	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	2.88	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



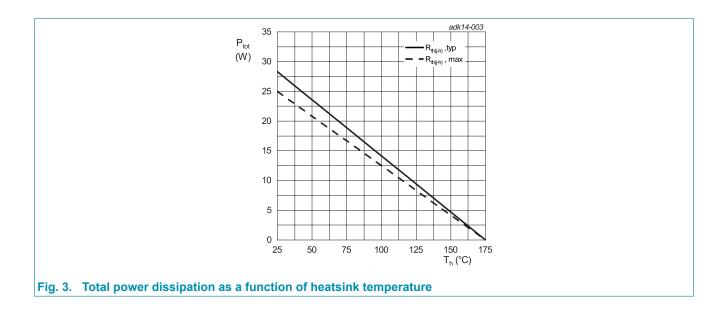
I_{F(AV)} = I_{F(RMS)} × √δ
 V_o = 0.895 V; R_s = 0.2583 Ω
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values





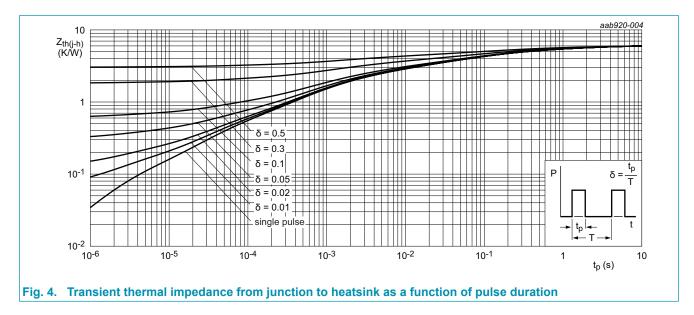
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9. Thermal characteristics

Symbol	ermal characteristics Parameter	Conditions	Min	Тур	Мах	Unit
Symbol	Falameter	Conditions	 IAILLI	тур	IVIAA	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; <u>Fig. 4</u>	-	5.3	6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

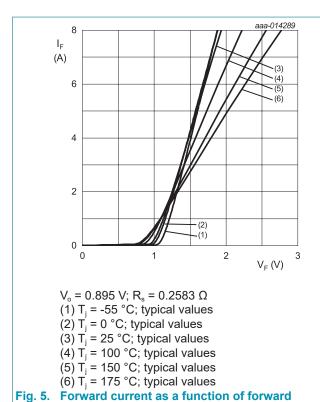


10. Isolation characteristics

Table 7. Isolation characteristics **Symbol** Parameter Conditions Min Unit Тур Max RMS isolation voltage from all terminals to external heatsink; 2500 V V_{isol(RMS)} _ _ sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; T_h = 25 °C; RH ≤ 65 %

11. Characteristics

	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 4 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I _F = 4 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V
I _R reverse current		V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	-	25	μA
		V _R = 650 V; T _j = 150 °C; <u>Fig. 6</u>	-	-	100	μA
Dynamic	characteristics		· · · · ·			
Q _r	recovered charge	I _F = 4 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	7	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	141	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	23	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	22	-	pF
E _{as}	non-repetitive	I _R = 3.5 A; T _{j(init)} = 25 °C; L = 5 mH	30	-	-	mJ
	avalanche energy					



voltage; typical values

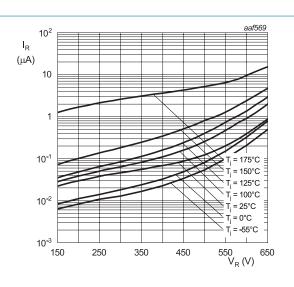
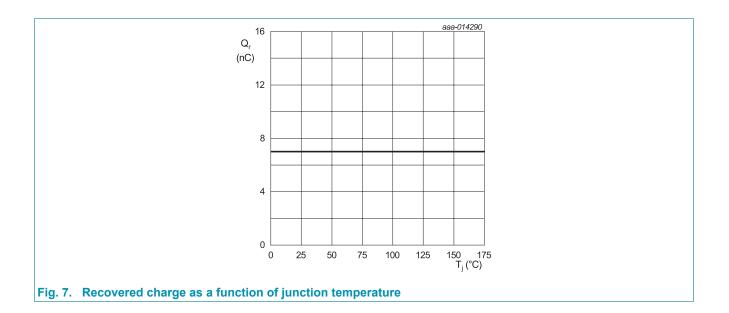


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

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12. Package outline

istic single-en	ded t	ihrou	gh-hol	e pac	kage; i	solated	heatsin	k mour	nted; 1	mountir	ig hole	; 2 -l ead	d TO-2	220F	TO220
Unit A		A1	b	b1	с	D	D1	е	Е	L	L1	L2	Р	q	Q
min 4.3	35 2	2.40	0.76	1.22	0.46	15.95	9.00	5 00	10.05	13.15	3.15	0.50	2.95	5 3.40	2.30
max 4.6	5 2	2.80	0.89	1.60	0.59	16.25	9.30	5.08 (typ.)	10.35	13.85	3.45	1.00	3.25	2 ±	2.80
OUTLINE			IEC		REI	FEREN	CES El/	AJ			EU PR	ROPE/ OJECT	AN TON	ISSUE	DATE
VERSION															

NXPSC04650X

Silicon Carbide Diode

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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